L	Hits	Search Text	DB	Time stamp
Number	211	shibata near2 kazutaka.in.	USPAT;	2004/06/10
*	211	Shibata hearz kazutaka.in.	US-PGPUB;	10:28
	ļ		EPO; JPO;	
			DERWENT;	
2	137	(shibata near2 kazutaka.in.) and resin	IBM_TDB USPAT;	2004/06/10
2	137	(Shidata hearz kazutaka.in.) and resin	US-PGPUB;	10:28
			EPO; JPO;	10.20
		<u> </u>	DERWENT;	
3	17	/(shibata mann) kamutaka in ) and masin)	IBM_TDB	2004/06/10
3	1,	((shibata near2 kazutaka.in.) and resin) and (polish\$4 or grind\$5)	USPAT; US-PGPUB;	2004/06/10
		(F	EPO; JPO;	10.50
			DERWENT;	
4	6	(((shibata near2 kazutaka.in.) and resin)	IBM_TDB	2004/06/10
1 3	8	and (polish\$4 or grind\$5)) and	USPAT; US-PGPUB;	2004/06/10
1		chip\$1on\$1chip	EPO; JPO;	10.00
			DERWENT;	
	15.00		IBM_TDB	2000/11/11
-	1569	resin same (polish\$ or grind\$) same (rear or back or back\$1side)	USPAT; US-PGPUB;	2003/11/18
		or saddifferen	EPO; JPO;	13.43
			DERWENT;	
_	755	regin game (neliable as assisted assisted	IBM_TDB	2007/11/10
] -	/33	resin same (polish\$ or grind\$) near10 (rear or back or back\$1side)	USPAT; US-PGPUB;	2003/11/18
		(Teal of back of backy151de)	EPO; JPO;	10.49
			DERWENT;	
	210		IBM_TDB	0000/44/40
-	318	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side)	USPAT; US-PGPUB;	2003/11/18
		(leaf of back of backylistice)	EPO; JPO;	10:49
			DERWENT;	1
		10 ( 11 10 )	IBM_TDB	
-	50	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) same	USPAT; US-PGPUB;	2003/11/18 16:56
		electrode	EPO; JPO;	10.30
	*		DERWENT;	
	172	magin magnio (maliché an animaté) annual	IBM_TDB	0000/11/10
	3	resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and	USPAT; US-PGPUB;	2003/11/18 17:53
	<b>*</b> *	semiconductor	EPO; JPO;	1,,,,,
1	•		DERWENT;	]
1_		resin near10 (polish\$ or grind\$) near10	IBM_TDB USPAT;	2003/11/18
		(rear or back or back\$lside) same chip	USPAT; US-PGPUB;	17:28
	ŕ	,, - <u></u>	EPO; JPO;	= -
			DERWENT;	i
-	5 (	ichikawa.in. near2 kimiya and resin same	IBM_TDB USPAT;	2003/11/18
	Ĭ	semiconductor	US-PGPUB;	17:22
	<b>₹</b>		EPO; JPO;	
	1		DERWENT;	
-	<sup>3</sup> 46	resin near10 (polish\$ or grind\$) near10	IBM_TDB USPAT;	2003/11/18
	10	(rear or back or back\$1side) near20	US-PGPUB;	17:53
]		expos\$	EPO; JPO;	
]	İ		DERWENT;	
-	172	resin near10 (polish\$ or grind\$) near10	<pre>IBM_TDB USPAT;</pre>	2003/11/18
[		(rear or back or back\$1side) and	US-PGPUB;	17:53
		semiconductor	EPO; JPO;	
]			DERWENT;	<b> </b>
-	131	resin near10 (polish\$ or grind\$) near10	<pre>IBM_TDB USPAT;</pre>	2003/11/18
		(rear or back or back\$1side) and chip	US-PGPUB;	18:12
			EPO; JPO;	
	}		DERWENT;	
L			IBM_TDB	

-	34	(resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) and chip) not ((resin near10 (polish\$ or grind\$)	USPAT; US-PGPUB; EPO; JPO;	2003/11/19 10:17
		near10 (rear or back or back\$1side) same electrode) or (resin near10 (polish\$ or grind\$) near10 (rear or back or	DERWENT; IBM_TDB	
		<pre>back\$1side) same chip) or (resin near10 (polish\$ or grind\$) near10 (rear or back or back\$1side) near20 expos\$))</pre>		
-	192	resin near10 (polish\$4 or grind\$) near10 thick\$ and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 10:18
-	44	resin near10 (polish\$4 or grind\$) near10 thick\$ same (back or back\$1side or rear) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 11:26
_	262	resin near10 (polish\$4 or grind\$) same (back or back\$1side or rear) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 10:40
-	172	resin near10 (polish\$4 or grind\$) near10 (back or back\$1side or rear) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 10:40
-	133	(back or back\$1side or rear) and semiconductor) not (resin near10 (polish\$4 or grind\$) near10 thick\$ same	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19
_	7	(back or back\$1side or rear) and semiconductor) resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor	IBM_TDB USPAT;	2003/11/19
		three, same bottom and semiconductor	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	11:28
_	54	resin near10 (polish\$4 or grind\$) near10 bottom and semiconductor not (resin near10 (polish\$4 or grind\$) near10 thick\$ same bottom and semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/11/19 11:49
<b>-</b>	2	02153527.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 11:50
_	1216	etch\$ same (grind\$ or polish\$) same resin	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19 13:02
_	150	etch\$ near10 (grind\$ or polish\$) near10 resin	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19
-	94.	etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/19
-	38	(etch\$ near10 (grind\$ or polish\$) near10 resin and @py<2002) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/19
			DERWENT; IBM_TDB	

		1 6 1 0 5 0 3 1		
-	2	6495914.pn.	USPAT;	2004/06/02
	•		US-PGPUB;	11:18
			EPO; JPO;	
1			DERWENT;	
İ			IBM_TDB	
-	0	chip adj on adj chip	USPAT;	2004/06/02
	•		US-PGPUB;	11:18
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	488	chip\$1on\$1chip	USPAT:	2004/06/02
		- ·	US-PGPUB;	11:19
			EPO; JPO;	·
			DERWENT;	
			IBM TDB	
-	240	chip\$1on\$1chip near5 structure	USPAT;	2004/06/02
			US-PGPUB;	11:20
			EPO; JPO;	111.20
			DERWENT;	
<b>!</b>			IBM TDB	İ
_	32	chip\$1on\$1chip near5 structure same	USPAT;	2004/06/02
	32	electrode	US-PGPUB;	11:25
		electione	EPO; JPO;	11:25
			DERWENT;	
ĺ				
_	54	chip\$lon\$lchip same resin	IBM_TDB	2004/06/00
_	24	chipsionsichip same resin	USPAT;	2004/06/02
			US-PGPUB;	11:44
			EPO; JPO;	
			DERWENT;	
	25		IBM_TDB	1 /
-	25	chip\$1on\$1chip near10 advantag\$5	USPAT;	2004/06/02
			US-PGPUB;	11:59
]			EPO; JPO;	[]
]			DERWENT;	j
j	_ [	50000	IBM_TDB	]
-	2	5977640.pn.	USPAT;	2004/06/02
			US-PGPUB;	11:59
	i		EPO; JPO;	
[			DERWENT;	į l
			IBM TDB	